

Transistors

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	$V_{GS}=\pm 12V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	–20	–	–	V	$I_D = -1mA, V_{GS}=0V$
Zero gate voltage drain current	I_{DSS}	–	–	–1	μA	$V_{DS} = -20V, V_{GS}=0V$
Gate threshold voltage	$V_{GS(th)}$	–0.7	–	–2.0	V	$V_{DS} = -10V, I_D = -1mA$
Static drain-source on-state resistance	$R_{DS(on)}$ *	–	50	70	mΩ	$I_D = -3.0A, V_{GS} = -4.5V$
		–	55	77	mΩ	$I_D = -3.0A, V_{GS} = -4V$
		–	90	125	mΩ	$I_D = -1.5A, V_{GS} = -2.5V$
Forward transfer admittance	$ Y_{fs} $ *	2.0	–	–	S	$V_{DS} = -10V, I_D = -1.5A$
Input capacitance	C_{iss}	–	760	–	pF	$V_{DS} = -10V$
Output capacitance	C_{oss}	–	125	–	pF	$V_{GS}=0V$
Reverse transfer capacitance	C_{rss}	–	100	–	pF	$f=1MHz$
Turn-on delay time	$t_{d(on)}$ *	–	12	–	ns	$I_D = -1.5A$
Rise time	t_r *	–	25	–	ns	$V_{DD} = -15V$
Turn-off delay time	$t_{d(off)}$ *	–	50	–	ns	$V_{GS} = -4.5V$
Fall time	t_f *	–	22	–	ns	$R_L=10\Omega$
Total gate charge	Q_g *	–	8.0	–	nC	$V_{DD} = -15V, R_L=5\Omega$
Gate-source charge	Q_{gs} *	–	1.5	–	nC	$V_{GS} = -4.5V, R_G=10\Omega$
Gate-drain charge	Q_{gd} *	–	2.5	–	nC	$I_D = -3A$

*Pulsed

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	–	–	–1.2	V	$I_S = -0.8A, V_{GS}=0V$

Transistors

●Electrical characteristic curves

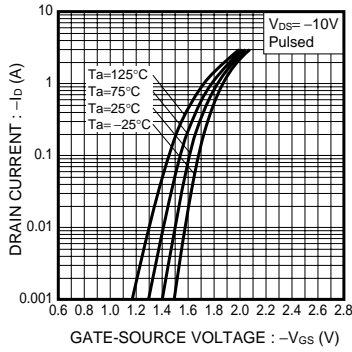


Fig.1 Typical Transfer Characteristics

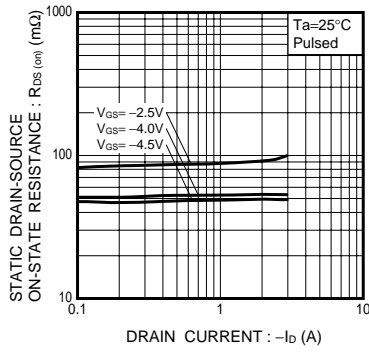


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

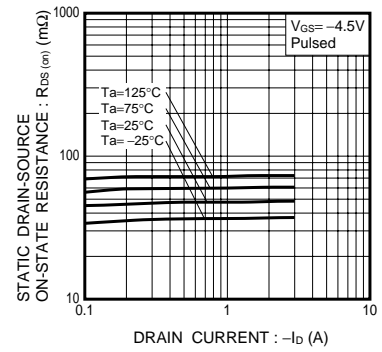


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

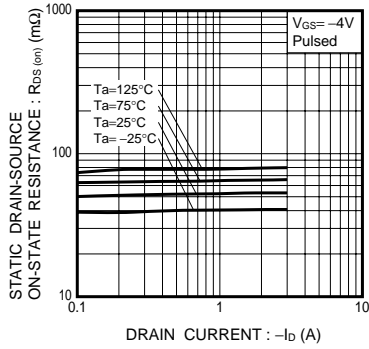


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

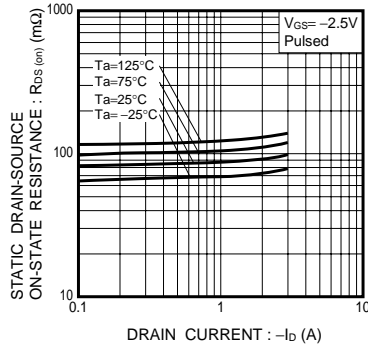


Fig.5 Static Drain-Source On-State Resistance vs. Drain Current

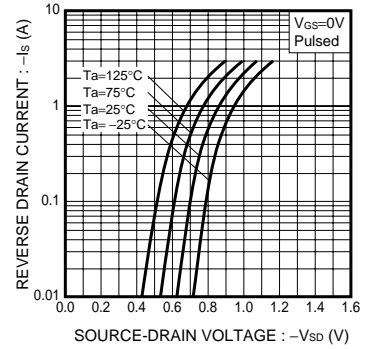


Fig.6 Reverse Drain Current vs. Source-Drain Voltage

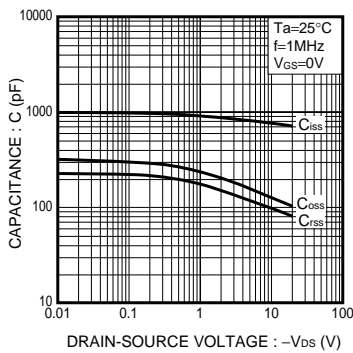


Fig.7 Typical Capacitance vs. Drain-Source Voltage

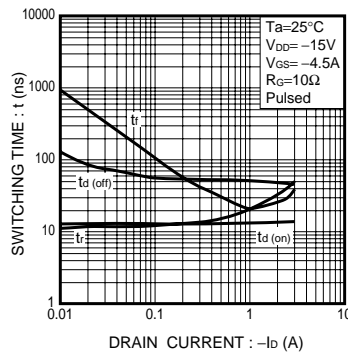


Fig.8 Switching Characteristics

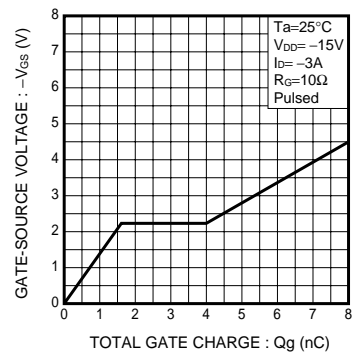


Fig.9 Dynamic Input Characteristics

Transistors

●Measurement circuits

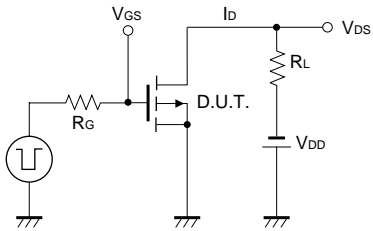


Fig.10 Switching Time Measurement Circuit

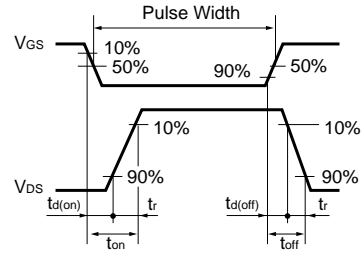


Fig.11 Switching Waveforms

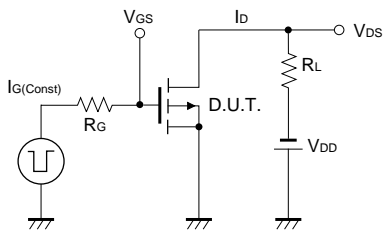


Fig.12 Gate Charge Measurement Circuit

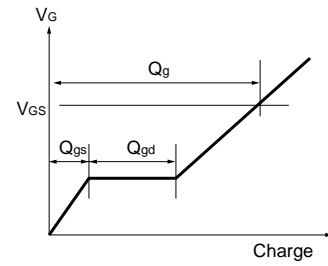


Fig.13 Gate Charge Waveforms

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